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In re Application of

TC 2800 MAIL ROOM

USAMI, Tatsuya

Serial No.: 09/627,418

Group Art Unit: 2814

Filed: July 27, 2000

Examiner: Quach, T.

For: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated November 20, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 4, as follows:

1. (Amended) A semiconductor device comprising:

a first interlayer insulating layer;

a plurality of wiring lines which are formed of Cu whose concentration is equal to or higher than 10^{19} atoms/cm³, said plurality of wiring lines formed on said first interlayer insulating layer;

an insulating layer which has a property that Cu is unlikely to enter said insulating layer and which insulates between said plurality of wiring lines; and

a second interlayer insulating layer formed on said insulating layer having a property

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that Cu is unlikely to enter therein.

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Adjusted date: 08/14/2003 SDIRET
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